NSN 5961-01-177-1327

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Inclosure Material:

Metal

Overall Length:

1.573 inches

Overall Height:

0.350 inches

Overall Width:

1.050 inches

End Application:

Radar bomb directing set an/tpb-1d

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-3

Mounting Method:

Unthreaded hole

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

700.0 breakdown voltage, collector-to-base, emitter open and 300.0 breakdown voltage, collector-to-emitter, base open and 5.0

breakdown voltage, emitter-to-base, collector open

Current Rating Per Characteristic:

10.00 amperes source cutoff current

Power Rating Per Characteristic:

125.0 watts small-signal input power, common-collector absolute

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

Junction pattern arrangement: npn

Terminal Type And Quantity:

2 pin and 1 case

Specification Data:

12115-8103-7121 manufacturers source control

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

A110a0